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(57) **ABSTRACT**

A liner is formed laterally-outside of individual channel-material strings in one of first tiers and in one of second tiers. The liners are isotropically etched to form void-spaces in the one second tier above the one first tier. Individual of the void-spaces are laterally-between the individual channel-material strings and the second-tier material in the one second tier. Conductively-doped semiconductive material is formed against sidewalls of the channel material of the channel-material strings in the one first tier and that extends upwardly into the void-spaces in the one second tier. The conductively-doped semiconductive material is heated to diffuse conductivity-increasing dopants therein from the void-spaces laterally into the channel material laterally there-adjacent and upwardly into the channel material that is above the void-spaces.

